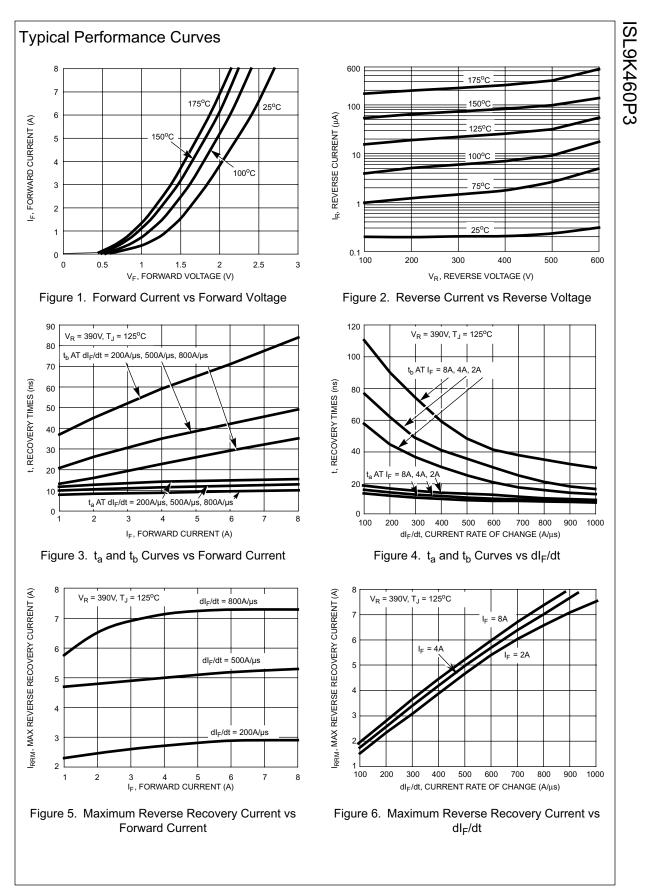
| | DUCTOR® | | Janu | uary 2002 |
|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------|----------------------------------------------|
| SL9K4 | 60P3 | | | |
| A, 600V | Stealth™ Dual Diode | | | |
| or low loss per witched appl everse recov ecovery under his device is oost diode in witching app educe loss in hinimizes ring nder which th f additional s stealth™ dioc nost efficient ower cost. | PP3 is a Stealth [™] dual diode optimized erformance in high frequency hard ications. The Stealth [™] family exhibits low ery current (I _{RRM}) and exceptionally soft er typical operating conditions. intended for use as a free wheeling or power supplies and other power lications. The low I _{RRM} and short t _a phase switching transistors. The soft recovery ging, expanding the range of conditions he diode may be operated without the use nubber circuitry. Consider using the le with an SMPS IGBT to provide the and highest power density design at elopmental type TA49408. | Features Soft Recovery Fast Recovery Operating Temperature Reverse Voltage Avalanche Energy Rate Applications Switch Mode Power Su Hard Switched PFC Bo UPS Free Wheeling Dia Motor Drive FWD SMPS FWD | pplies ost Diode | t _{rr} < 20ns 175 ^o C |
| | | Snubber Diode | | |
| Package | JEDEC TO-220AB | Symbol | | |
| | | cunless otherwise noted | | A ₂ |
| Symbol | Parameter | | Ratings | Units |
| V _{RRM} | Peak Repetitive Reverse Voltage | 600 | V | |
| V _{RWM} | Working Peak Reverse Voltage | 600 | V | |
| V _R | DC Blocking Voltage | 600 | V | |
| I _{F(AV)} | Average Rectified Forward Current Total Device Current (Both Legs) | 4 8 | AA | |
| I _{FRM} | Repetitive Peak Surge Current (20kHz Squar | 8 | A | |
| I _{FSM} | Nonrepetitive Peak Surge Current (Halfwave | 50 | A | |
| P _D | Power Dissipation | | 58 | W |
| E _{AVL} | Avalanche Energy (1A, 20mH) | | 10 | mJ |
| T _J , T _{STG} | Operating and Storage Temperature Range | | -55 to 175 | °C |
| T _L T _{PKG} | Maximum Temperature for Soldering | | | °C |

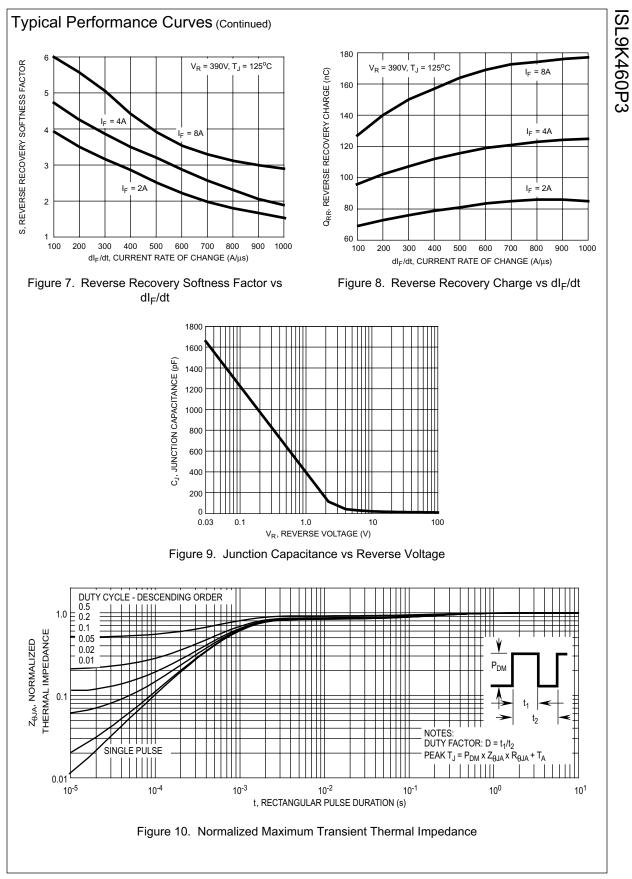
CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

| Device Marking K460P3 | | Device ISL9K460P3 | Package Tape Width TO-220AB - | | 1 | | Quantity | |
|----------------------------------------|----------------------------------------------|---------------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------------|-----|------------|----------|---------|
| | | | ļ | | | | | |
| | al Chara | cteristics (per leg) T _c = | | | | _ | | |
| Symbol | | Parameter | Test Co | onditions | Min | Тур | Max | Unit |
| Off State | Character | istics | | | | | | |
| I _R | I _R Instantaneous Reverse Current | | V _R = 600V | T _C = 25°C | - | - | 100 | μA |
| | | | | T _C = 125°C | - | - | 1.0 | mA |
| On State | Character | istics | | | | | | |
| V _F | | | I _F = 4A | T _C = 25°C | - | 2.0 | 2.4 | V |
| · F | | | | $T_{\rm C} = 125^{\circ}{\rm C}$ | - | 1.6 | 2.0 | V |
| | | · · · · · | | | | | | |
| • | Character | | | | i | | | |
| CJ | Junction Ca | apacitance | V _R = 10V, I _F = 0A | | - | 19 | - | pF |
| Switching | g Characte | eristics | | | | | | |
| t _{rr} | Reverse Recovery Time | | I _F = 1A, d _{IF} /dt = 100A/μs, V _R = 30V | | - | 17 | 20 | ns |
| | | | $I_{\rm F} = 4A, d_{\rm IF}/dt = 100A/\mu s, V_{\rm R} = 30V$ | | - | 19 | 22 | ns |
| t _{rr} | Reverse Re | ecovery Time | $I_{F} = 4A,$ $d_{IF}/dt = 200A/\mu s,$ $V_{R} = 390V, T_{C} = 25^{\circ}C$ $I_{F} = 4A,$ $d_{IF}/dt = 200A/\mu s,$ $V_{R} = 390V,$ $T_{C} = 125^{\circ}C$ $I_{F} = 4A,$ $d_{IF}/dt = 400A/\mu s,$ $V_{R} = 390V,$ $T_{C} = 125^{\circ}C$ | | - | 17 | - | ns |
| I _{RRM} | Maximum F | Reverse Recovery Current | | | - | 2.6 | - | Α |
| Q_{RR} | Reverse Re | ecovery Charge | | | - | 22 | - | nC |
| t _{rr} | Reverse Re | ecovery Time | | | - | 77 | - | ns |
| S | Softness Fa | | | | - | 4.2 | - | |
| I _{RRM} | | Reverse Recovery Current | | | - | 2.8 | - | A |
| Q _{RR} | | ecovery Charge | | | - | 100 | - | nC |
| t _{rr} | | ecovery Time | | | - | 54 | - | ns |
| <u> </u> | Softness Fa | | | | - | 3.5 | - | |
| I _{RRM} | | Reverse Recovery Current | | | - | 4.3 110 | - | A nC |
| Q _{RR} dI _M /dt | | li/dt during t _b | | | _ | 500 | - | A/µ |
| | | | | | | 000 | | 7.0 Pr |
| hermal | Characteri | stics | | | | | | |
| $R_{	extsf{	heta}JC}$ | _ | esistance Junction to Case | | | - | - | 2.6 | °C/V |
| R_{\thetaJA} | Thermal Re | esistance Junction to Ambient | TO-220AB | | - | - | 62 | °C/V |

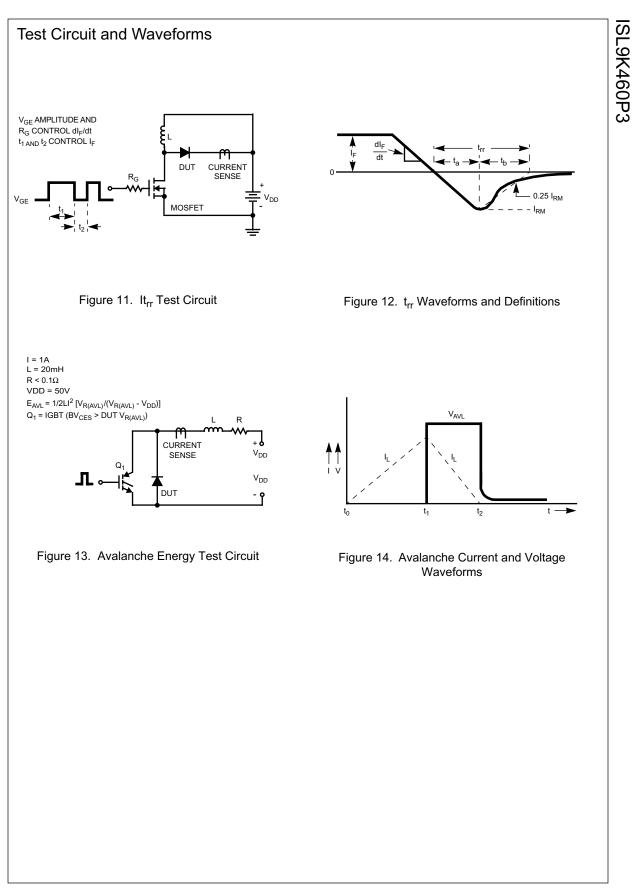
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